

HK303X, HK304X, HK306X, HK308X

6-Pin DIP Zero-Cross Triac Driver Photocouplers

Description

The HK303X, HK304X, HK306X, HK308X series of devices each consists of a GaAs infrared emitting diode optically coupled to a monolithic silicon Zero-Cross photo Triac.

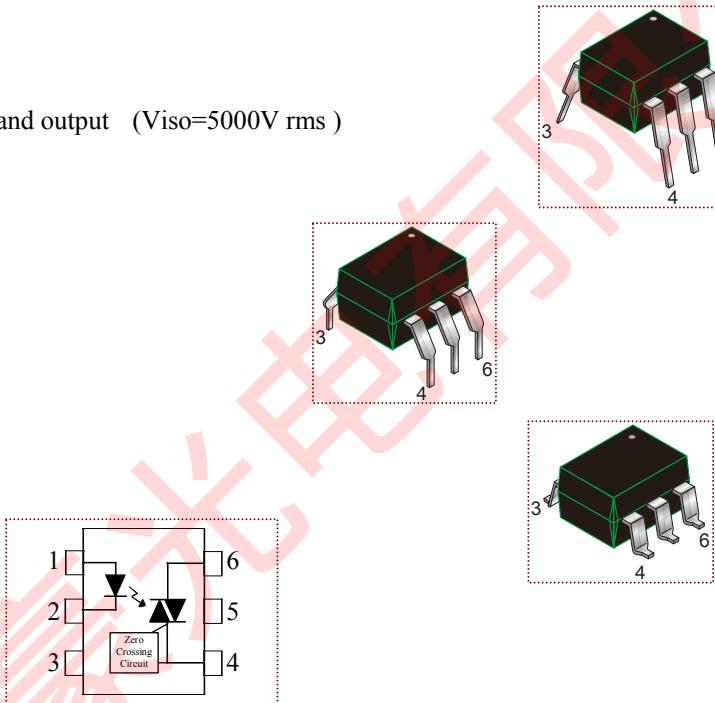
Features

- Peak breakdown voltage,
 - 250V: HK303X
 - 400V: HK304X
 - 600V: HK306X
 - 800V: HK308X
- High isolation voltage between input and output (Viso=5000V rms)
- Zero voltage crossing
- Compact dual-in-line package
- Pb free and RoHS compliant.
- UL approved
- VDE approved

Applications

- Solenoid/valve controls
- Light controls
- Static power switch
- AC motor drivers
- E.M. contactors
- Temperature controls
- AC Motor starters
- Solid state relays

Block Diagram and Package



Absolute Maximum Ratings (Ta=25°C)

Parameter		Symbol	Rating	Unit
Input	Forward Current	I _F	60	mA
	Reverse Voltage	V _R	6	V
	Power Dissipation	P _D	100	mW
	Derating Factor (above Ta = 85°C)		3.8	mW/°C
Output	Off-state Output Terminal Voltage	V _{DRM}	250	V
	HK303X		400	
	HK304X		600	
	HK306X		800	
	Peak Repetitive Surge Current (pw=100μs,120ppps)	I _{TSM}	1	A
	On-State RMS Current	I _{T(RMS)}	100	mA
	Power Dissipation	P _C	300	mW
	Derating Factor (above Ta = 85°C)		7.6	mW/°C
Total Power Dissipation		P _{tot}	330	mW
Isolation Voltage *		V _{iso}	5000	Vrms
Operating Temperature		T _{opr}	-55~+100	°C



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Parameter	Symbol	Rating	Unit
Storage Temperature	T _{stg}	-55~+125	°C
Soldering Temperature (10s)	T _{sol}	260	°C

* AC for 1 minute, R.H.= 40 ~ 60% R.H. In this test, pins 1, 2 & 3 are shorted together, and pins 4, 5 & 6 are shorted together.

Electro-optical Characteristics (Ta=25°C, unless specified otherwise)

Parameter		Symbol	Condition	Min.	Typ.	Max.	Unit
Input	Forward Voltage	V _F	I _F =30mA	-	-	1.5	V
	Reverse Current	I _R	V _R =6V	-	-	10	μA
Output	Peak Blocking Current	HK303X HK304X HK306X HK308X	I _{DRM1}	V _{DRM} = Rated	-	-	100
				V _{DRM} , I _F = 0mA	-	-	500
	Peak On-state Voltage	V _{TM}	I _{TM} =100mA peak, I _F =Rated I _{FT}	-	-	3	V
	Critical Rate of Rise off-state Voltage	HK303X HK304X HK306X HK308X	dv/dt	V _{PEAK} = Rated	1000	-	-
	Inhibit Voltage (MT1-MT2 voltage above which device will not trigger)			V _{DRM} , I _F =0	600	-	-
	Leakage in Inhibited State	I _{DRM2}	I _F = Rated I _{FT} , V _{DRM} =Rated V _{DRM} , off state	-	-	500	μA
Transfer Characteristics	LED Trigger Current	HK3031 HK3041 HK3061 HK3081 HK3032 HK3042 HK3062 HK3082 HK3033 HK3043 HK3063 HK3083	I _{FT}	Main terminal Voltage=3V	-	-	15
					-	-	10
					-	-	5
	Holding Current	I _H		-	280	-	μA



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Typical Electro-Optical Characteristics Curves

Fig.1 LED Forward Voltage vs Forward Current

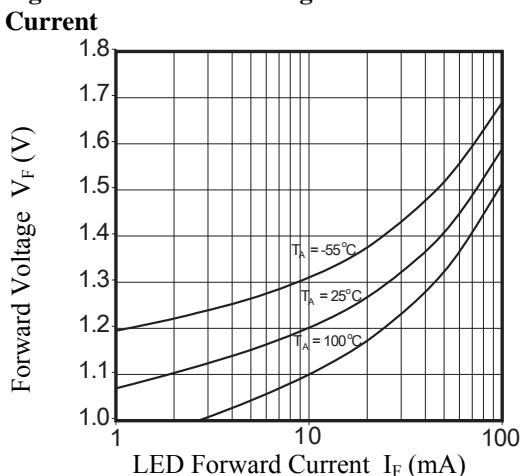


Fig.2 On-State Characteristics

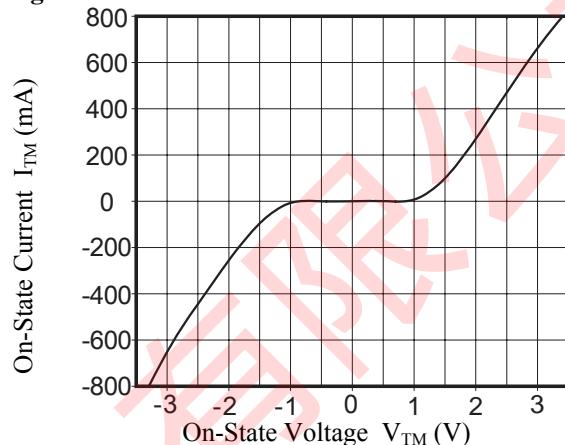


Fig.3 Trigger Current vs. Ambient Temperature

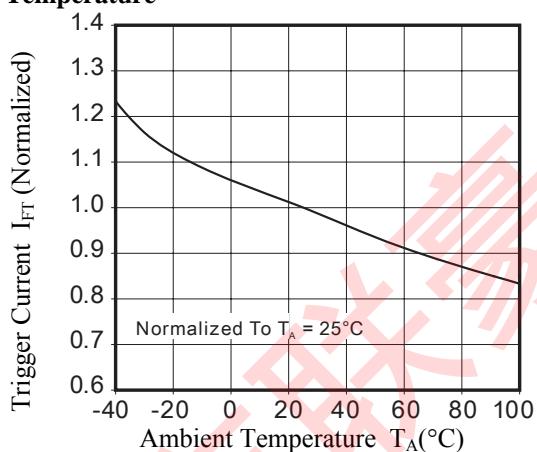


Fig.4 LED Current Required to Trigger vs. LED Pulse Width

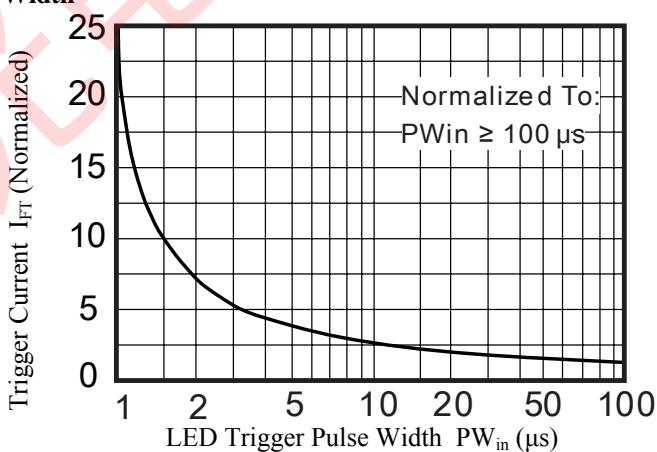


Fig.5 Holding Current vs. Temperature

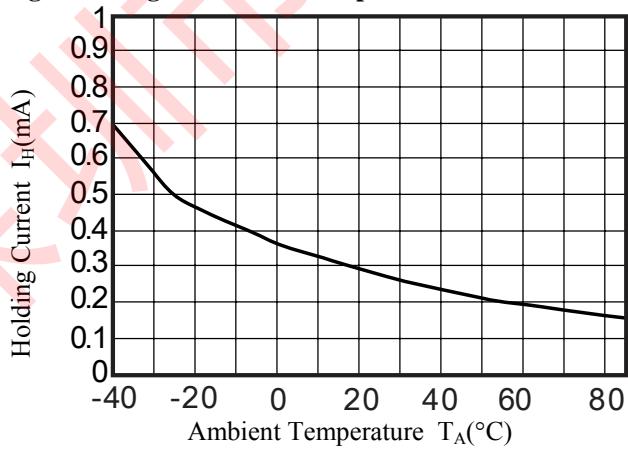
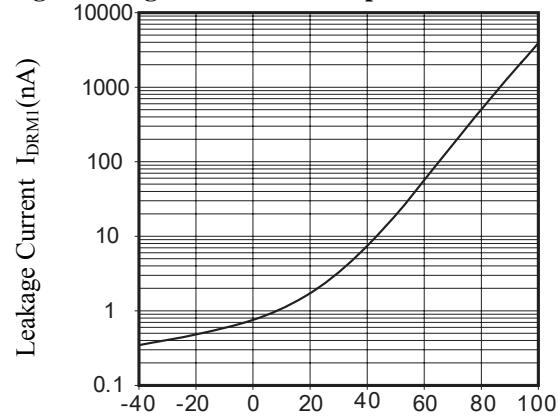


Fig.6 Leakage Current vs. Temperature





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Fig.7 I_{DRM2} , Leakage in Inhibit State vs. Temperature

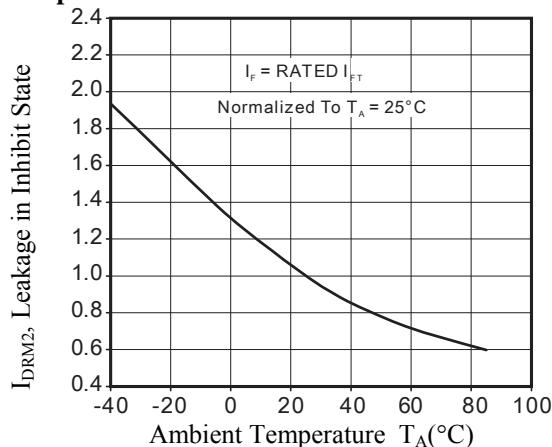


Fig.8 Inhibit Voltage vs. Temperature

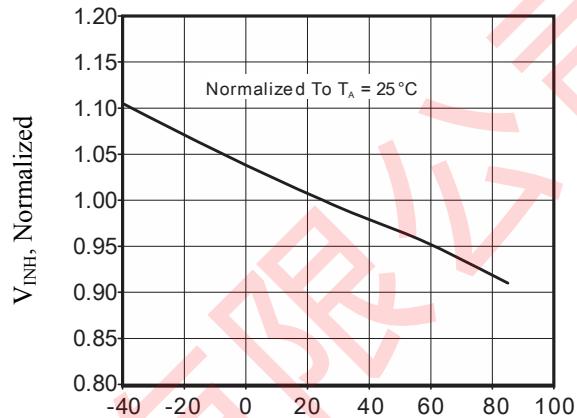
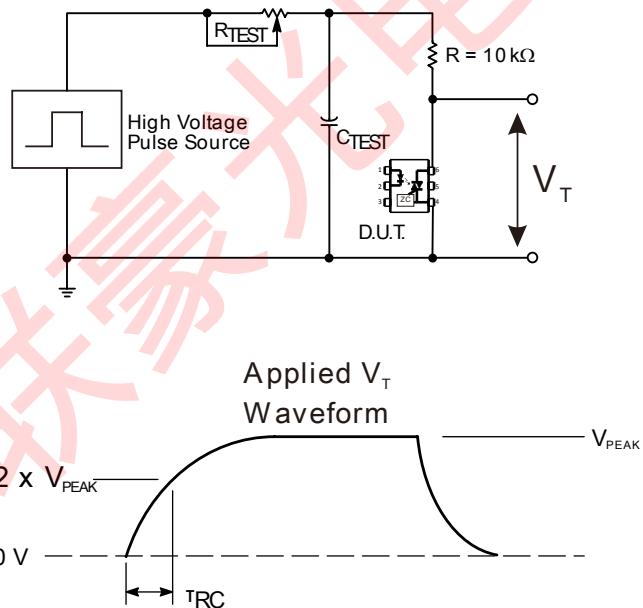


Fig.9 Static dv/dt Test Circuit & Waveform



The high voltage pulse is set to the required V_{PEAK} value and applied to the D.U.T. output side through the RC circuit above. LED current is not applied. The waveform V_T is monitored using an x100 scope probe. By varying R_{TEST} , the dv/dt (slope) is increased, until the D.U.T. is observed to trigger (waveform collapses). The dv/dt is then decreased until the D.U.T. stops triggering. At this point, τ_{RC} is recorded and the dv/dt calculated.

$$dv/dt = \frac{0.632 \times V_{PEAK}}{\tau_{RC}}$$

For example, $V_{PEAK} = 400\text{V}$ for HK304X series. The dv/dt value is calculated as follows:

$$dv/dt = \frac{0.632 \times 400}{\tau_{RC}} = \frac{252}{\tau_{RC}}$$



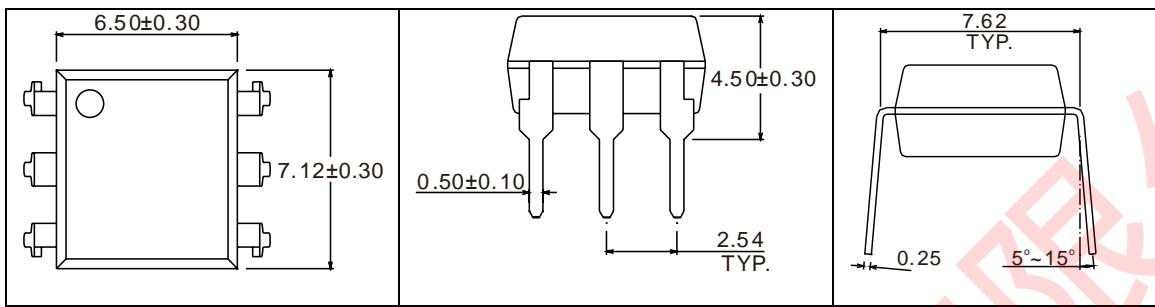
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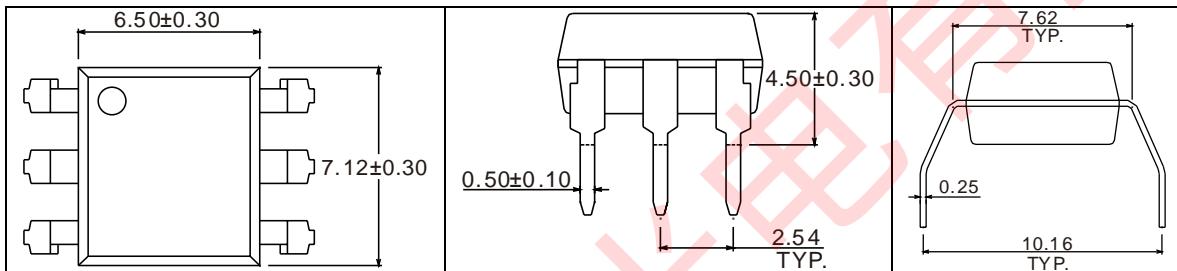
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Outline Dimensions

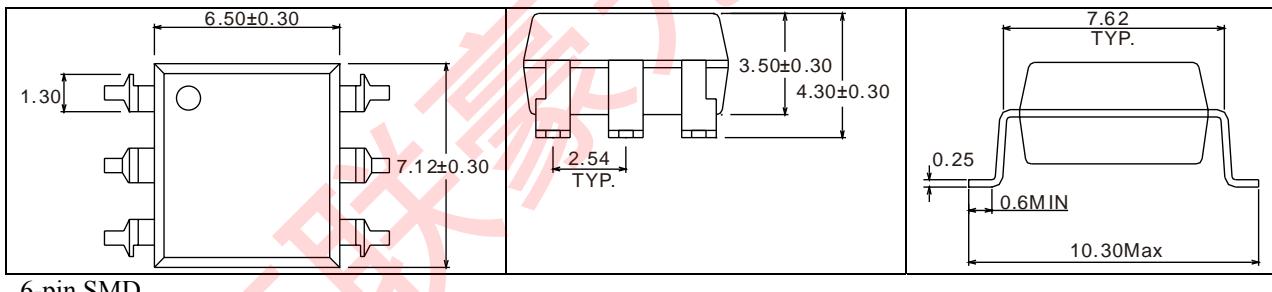
Unit: mm



6-pin DIP



6-pin DIP (M Type)



6-pin SMD



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Marking

HK30VT
YYWW

- “V” denotes V_{DRM} digit: 3/4/6/8; “T” denotes I_{FT} digit: 1/2/3
- “YY” denotes YEAR; “WW” denotes WEEK

Device Table

Part Name	Main Marking	Package
HK3031D/M/S	HK3031	6-pin DIP / 6-pin DIP (M Type) / 6-pin SMD
HK3032D/M/S	HK3032	6-pin DIP / 6-pin DIP (M Type) / 6-pin SMD
HK3033D/M/S	HK3033	6-pin DIP / 6-pin DIP (M Type) / 6-pin SMD
HK3041D/M/S	HK3041	6-pin DIP / 6-pin DIP (M Type) / 6-pin SMD
HK3042D/M/S	HK3042	6-pin DIP / 6-pin DIP (M Type) / 6-pin SMD
HK3043D/M/S	HK3043	6-pin DIP / 6-pin DIP (M Type) / 6-pin SMD
HK3061D/M/S	HK3061	6-pin DIP / 6-pin DIP (M Type) / 6-pin SMD
HK3062D/M/S	HK3062	6-pin DIP / 6-pin DIP (M Type) / 6-pin SMD
HK3063D/M/S	HK3063	6-pin DIP / 6-pin DIP (M Type) / 6-pin SMD
HK3081D/M/S	HK3081	6-pin DIP / 6-pin DIP (M Type) / 6-pin SMD
HK3082D/M/S	HK3082	6-pin DIP / 6-pin DIP (M Type) / 6-pin SMD
HK3083D/M/S	HK3083	6-pin DIP / 6-pin DIP (M Type) / 6-pin SMD

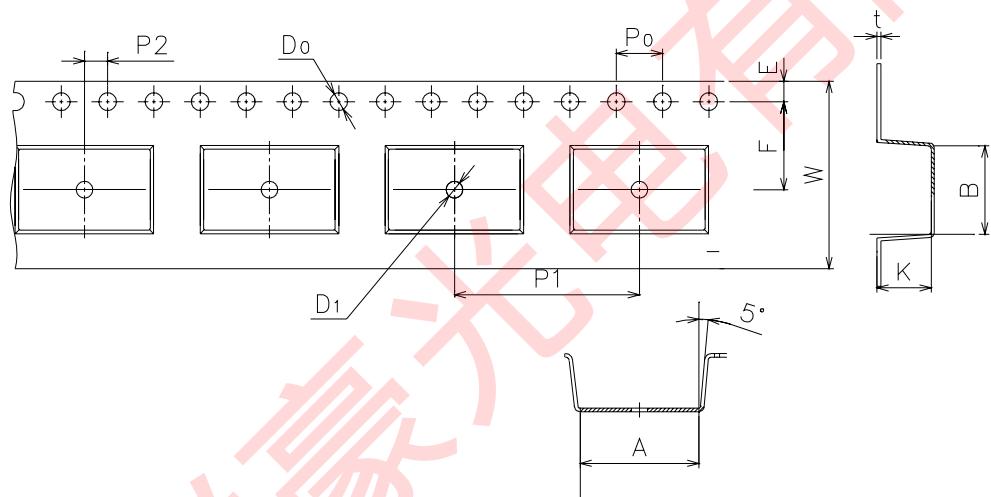
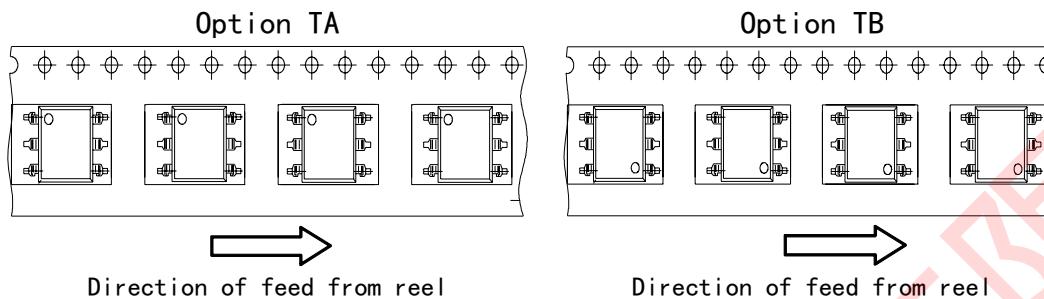


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Tape & Reel Packing



Dimension No.	A	B	D0	D1	E	F
Dimension (mm)	10.4±0.1	7.5±0.1	1.5±0.1	1.5+0.1/-0	1.75±0.1	7.5±0.1

Dimension No.	P0	P1	P2	t	W	K
Dimension (mm)	4.0±0.15	12±0.1	2.0±0.1	0.35±0.03	16.0±0.2	4.5±0.1



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